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(54) **THIN FILM DIELECTRICS FOR CAPACITORS AND METHODS OF MAKING THEREOF**

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See application file for complete search history.

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(57) **ABSTRACT**

Dielectrics are formed having high dielectric constants, low loss tangents, and other desirable electrical and physical properties. The dielectrics are annealed at temperatures allowing the use of copper foil substrates, and at low oxygen partial pressures.

**28 Claims, 8 Drawing Sheets**

